

Paula Diaz Reigosa

List of Publications by Year in descending order

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30
papers

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839539

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times ranked

507
citing authors

| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 1 | Prediction of Bond Wire Fatigue of IGBTs in a PV Inverter under a Long-Term Operation. IEEE Transactions on Power Electronics, 2015, , 1-1. | 7.9 | 128 |
| 2 | A Short-Circuit Safe Operation Area Identification Criterion for SiC MOSFET Power Modules. IEEE Transactions on Industry Applications, 2017, 53, 2880-2887. | 4.9 | 78 |
| 3 | A survey of SiC power MOSFETs short-circuit robustness and failure mode analysis. Microelectronics Reliability, 2017, 76-77, 272-276. | 1.7 | 68 |
| 4 | Effect of short-circuit stress on the degradation of the SiO ₂ dielectric in SiC power MOSFETs. Microelectronics Reliability, 2018, 88-90, 577-583. | 1.7 | 35 |
| 5 | Impact of Repetitive Short-Circuit Tests on the Normal Operation of SiC MOSFETs Considering Case Temperature Influence. IEEE Journal of Emerging and Selected Topics in Power Electronics, 2020, 8, 195-205. | 5.4 | 31 |
| 6 | A humidity-dependent lifetime derating factor for DC film capacitors. , 2015, , . | | 27 |
| 7 | Modern IGBT gate driving methods for enhancing reliability of high-power converters " An overview. Microelectronics Reliability, 2016, 58, 141-150. | 1.7 | 25 |
| 8 | Implications of Ageing Through Power Cycling on the Short-Circuit Robustness of 1.2-kV SiC mosfets. IEEE Transactions on Power Electronics, 2019, 34, 11182-11190. | 7.9 | 22 |
| 9 | Robustness of MW-Level IGBT modules against gate oscillations under short circuit events. Microelectronics Reliability, 2015, 55, 1950-1955. | 1.7 | 20 |
| 10 | Study on Oscillations During Short Circuit of MW-Scale IGBT Power Modules by Means of a 6-kA/1.1-kV Nondestructive Testing System. IEEE Journal of Emerging and Selected Topics in Power Electronics, 2015, 3, 756-765. | 5.4 | 17 |
| 11 | Improving the Short-Circuit Reliability in IGBTs: How to Mitigate Oscillations. IEEE Transactions on Power Electronics, 2018, 33, 5603-5612. | 7.9 | 17 |
| 12 | On-line solder layer degradation measurement for SiC-MOSFET modules under accelerated power cycling condition. Microelectronics Reliability, 2018, 88-90, 563-567. | 1.7 | 17 |
| 13 | Investigation on the degradation indicators of short-circuit tests in 1.2-kV SiC MOSFET power modules. Microelectronics Reliability, 2018, 88-90, 661-665. | 1.7 | 11 |
| 14 | New layout concepts in MW-scale IGBT modules for higher robustness during normal and abnormal operations. , 2016, , . | | 8 |
| 15 | Impact of meteorological variations on the lifetime of grid-connected PV inverters. Microelectronics Reliability, 2018, 88-90, 1019-1024. | 1.7 | 8 |
| 16 | Impact of the Case Temperature on the Reliability of SiC MOSFETs Under Repetitive Short Circuit Tests. , 2019, , . | | 8 |
| 17 | Compact electro-thermal modeling of a SiC MOSFET power module under short-circuit conditions. , 2017, , . | | 7 |
| 18 | Failure Analysis of a Degraded 1.2 kV SiC MOSFET after Short Circuit at High Temperature. , 2018, , . | | 7 |

| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 19 | Investigation on the short circuit safe operation area of SiC MOSFET power modules. , 2016, , . | | 6 |
| 20 | Switching Stability Analysis of Paralleled RC-IGBTs With Snapback Effect. IEEE Transactions on Electron Devices, 2021, 68, 3429-3434. | 3.0 | 6 |
| 21 | TCAD analysis of short-circuit oscillations in IGBTs. , 2017, , . | | 5 |
| 22 | Increasing emitter efficiency in 3.3-kV enhanced trench IGBTs for higher short-circuit capability. , 2018, , . | | 5 |
| 23 | Capacitive effects in IGBTs limiting their reliability under short circuit. Microelectronics Reliability, 2017, 76-77, 485-489. | 1.7 | 4 |
| 24 | Modeling of IGBT With High Bipolar Gain for Mitigating Gate Voltage Oscillations During Short Circuit. IEEE Journal of Emerging and Selected Topics in Power Electronics, 2019, 7, 1584-1592. | 5.4 | 4 |
| 25 | Implications of short-circuit events on power cycling of 1.2-kV/20-A SiC MOSFET power modules. Microelectronics Reliability, 2019, 100-101, 113373. | 1.7 | 4 |
| 26 | Short-circuit robustness of retrograde channel doping 1.2-kV SiC MOSFETs. Microelectronics Reliability, 2021, 120, 114117. | 1.7 | 4 |
| 27 | Tvindkraft: Implementing a 500 kW 21-IGBT-based frequency converter for a 1.7 MW wind power conversion system. , 2013, , . | | 3 |
| 28 | Non-uniform Temperature Distribution Implications on Thermal Analysis Accuracy of Si IGBTs and SiC MOSFETs. , 2018, , . | | 3 |
| 29 | Approaching repetitive short circuit tests on MW-scale power modules by means of an automatic testing setup. , 2016, , . | | 0 |
| 30 | Effects of the HV-BIGT Design Elements on the High-Frequency Oscillation Instability during Short Circuit Transients. , 2019, , . | | 0 |